Abstracts

Monolithic FET Structures for High-Power Control Component Applications

M.B. Shifrin, P.J. Katzin and Y. Ayasli. "Monolithic FET Structures for High-Power Control Component Applications." 1989 Transactions on Microwave Theory and Techniques 37.12 (Dec. 1989 [T-MTT] (1989 Symposium Issue)): 2134-2141.

A new monolithic switch FET control circuit has been developed that can be integrated with other monolithic functions or used as a discrete component in an MIC structure. This device increases the power-handling capability of the conventional single FET switch by an order of magnitude. It does this by overcoming the breakdown voltage limitation of the FET device. The design, fabrication, and performance of two high-power control components using these circuits are described as examples of the implementation of this technology (an L-band terminated single-pole single throw (SPST) switch and an L-band limiter).

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